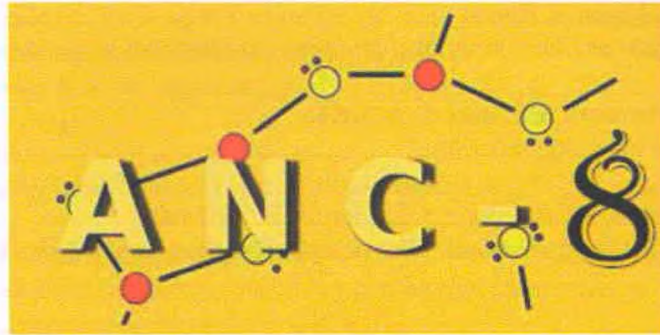


Abstract Book

**8th International Conference on
Amorphous and Nanostructured Chalcogenides**

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Contents

Invited Papers

P. Boolchand <i>Correlating melt dynamics with glass topological phases in chalcogenides</i>	1
L. Calvez <i>Ga-based chalcogenide glass-ceramics transparent in the infrared</i>	1
E. A. Chechetkina <i>Bond waves in thin films: Photostructural changes and electrical switching in amorphous chalcogenides</i>	2
S. Hosokawa, J. R. Stellhorn <i>Local structural analysis for chalcogenide functional materials</i>	2
G. Kaur Ahluwalia <i>Applications of Chalcogenides S, Se and Te</i>	3
S. Kökényesi <i>Plasmon assisted optical recording in amorphous nanocomposites</i>	4
A. Kovalskiy, R. Golovchak, M. White, J. Allen, L. Nicholls, K. Palka, M. Vlcek, H. Jain <i>In situ kinetics of photoinduced effects in thermally deposited and spin-coated chalcogenide glass thin films</i>	5
A. A. Kryuchyn, V. V. Petrov, V. M. Rubish, M. L. Trunov, S. A. Kostyukevich <i>Formation of nanoscale structures on chalcogenide films</i>	5
S. Kugler <i>Photoinduced bond breaking and volume change in chalcogenide glasses</i>	6
V. S. Minaev <i>Polymorphism and intermediate-range order – the basis of the structure of glassy and non-glassy of non-crystalline individual chemical substances</i>	6
N. Mousseau <i>Understanding the long-time kinetics of disordered and complex materials with the kinetic activation-relaxation technique</i>	7
T. Nichol, M. R. Latif, M. Ailavjhala, M. Mitkova <i>Interaction of Ge-Se films with ions: Structural studies and application for memory arrays formation</i>	7

A. Piarristeguy, A. Pradel, P. Jóvári, I. Kaban <i>Te-based chalcogenide amorphous films: structural and physico-chemical properties</i>	8
M. Popescu, F. Sava, I.D. Simandan, A. Lőrinczi, A. Velea <i>Freestanding thin amorphous chalcogenide films</i>	9
J. Rocca, V. Bilovol, M. Fontana, M. A. Ureña, J. L. García, B. Arcondo <i>Chalcogenide glasses for PCRAM applications. Characterization from large to short range order</i>	9
J. Singh <i>Excitons to photocarrier generations in bulk heterojunction organic solar cells</i>	10
J. Teteris <i>Photoinduced mass transport in amorphous chalcogenide and azobenzene organic materials</i>	10
D. Tsiulyanu <i>Remarks on surface and transport phenomena in chalcogenide glassy semiconductors</i>	11
A. Velea, K. Opsomer, W. Devulder, J. Dumortier, J. Fan, C. Detavernier, M. Jurczak, B. Govoreanu <i>Chalcogenide materials for selectors and phase change memories</i>	12
M. Wuttig <i>Novel phase change materials by design: the mystery of resonance bonding</i>	13

Regular Papers – Oral Session

P. E. Agbo, P. A. Nwofe, L. O. Odo <i>Effect of dye addition on the structural and optical properties of AlZnS thin films</i>	14
R. I. Alekberov, M. Fabián, A. I. Isayev, S. I. Mekhtiyeva <i>The local structure and optical properties of $As_{40}Se_{60}$, $As_{40}Se_{30}S_{30}$, $As_{40}Se_{30}Te_{30}$ chalcogenide glasses</i>	14
D. K. Dwivedi <i>Selenium based semiconducting non-oxide glasses for optical data storage</i>	15
S. Dyussebaev, O. Prikhodko, A. Sazonov, Z. Tolepov, N. Almasov, S. Maksimova, N. Guseinov, S. Kozyukhin <i>Electronic properties of nanosized $Ge_2Sb_2Te_5 < Bi >$ films</i>	16
S. Kozyukhin, Yu. Vorobyov, P. Lazarenko, M. Presniakov, A. Pevtsov <i>Isothermal and laser crystallization of amorphous $Ge_2Sb_2Te_5$ thin films</i>	17
M. Kristl, S. Gyergyek, J. Kristl <i>Nanostructured nickel sulfides with different stoichiometries prepared by mechanochemical synthesis</i>	17
V. Mitsa, A. Feher, S. Petretskij, R. Holomb, V. Tkac <i>Hysteresis of low temperature thermal conductivity, Boson peak in glassy (g) As_2S_3 and low frequency ring and branched $AsnSm$ clusters vibrations</i>	18
G. Osayemwenre, E. Meyer, T. R. Taziwa <i>Stress analysis in a degraded monocrystalline solar cell by Raman Spectroscopy</i>	18

A. Sherchenkov, S. Kozyukhin, A. Babich, P. Lazarenko, V. Kalugin, S. Timoshenkov <i>Crystallization mechanism and kinetic parameters in $Ge_2Sb_2Te_5$ thin films for the phase change memory application</i>	19
P. K. Singh, D. K. Dwivedi <i>Effect of thermal annealing on structural and optical properties of $Se_{66}Te_{25}In_9$ thin films</i>	19
J. R. Stellhorn, W.-C. Pilgrim, Y. Sutou, S. Hosokawa <i>A combination of anomalous X-ray scattering and X-ray absorption fine structure experiments for the characterization of amorphous $GeCu_2Te_3$</i>	20
V. I. Verlan, P. Bardetchi, O. Bordian, M. S. Iovu, I. Culeac, V. E. Zubareva <i>Energy transfer from UV to red in the polymer/nanocomposites with Eu^{3+} coordination compounds</i>	21

Regular Papers - Poster Session

I. Baník <i>Optical phenomena in chalcogenide glass-fibers illuminated with lateral excited band-gap light</i>	22
L. Baschir, C. Opran, D. Savastru, S. Miclos, A. Popescu <i>Spectroscopic ellipsometric study of As_2S_3 RF sputtered thin films</i>	22
V. Bilanych, V. Komanicky, A. Feher, V. Kuzma, V. Rizak <i>Dynamic Taylor cone formation on chalcogenide films surface</i>	23
V. Bilanych, V. Komanicky, M. Kozejova, A. Feher, A. Kovalcikova, F. Lofaj, V. Kuzma, V. Rizak <i>Influence of size factors on the formation of surface relief in amorphous chalcogenide films during periodic charge deposition by electronic beam</i>	23
V. Bilanych, K. Flachbart, A. Jurikova, K. Csach, V. Rizak <i>Relaxation processes in chalcogenide glasses</i>	24
E. A. Chechetkina <i>Ultrasound modulation of the structure of glassy chalcogenides</i>	24
M. Ciobanu <i>DC conductivity in As_2S_3 Ge_8Te_x amorphous thin films</i>	25
S. Cozic, A. Castro, O. Bošák, M. Kubliha, V. Labaš, L. Calvez, D. Le Coq <i>Synthesis and electrical characterization of Li-based sulfide glasses</i>	26
A. Duta, A. Enesca, D. Perniu, M. Covei, L. Isac <i>Low cost CZTS-type photovoltaic cells fully deposited by Spray Pyrolysis</i>	27
S. Hosokawa, Y. Ideguchi, K. Kamimura, N. Happo, K. Kimura, K. Hayashi, Y. Ebisu, T. Ozaki, Y. Yoda, H. Ishii, M. Kitaura, M. Sasak <i>An x-ray fluorescence holographic study on a $Bi_2Te_3:Mn$ topological insulator</i>	28
O. Iaseniuc, M. Iovu, O. Bordian <i>Steady-state and transient photoconductivity of some ternary amorphous thin films</i>	28

O. V. Iaseniuc, M. S. Iovu, D. Dinescu, M. Enachescu <i>Optical spectroscopy of $(As_4S_3Se_3)_{1-x}Sn_x$ and $Ge_xAs_xSe_{1-2x}$ chalcogenides</i>	29
Y. Ideguchi, J. R. Stellhorn, S. Hosokawa, N. Happo, K. Kimura, K. Hayashi, H. Okazaki, A. Yamashita, Y. Takano <i>X-ray fluorescence holographic study on high-temperature superconductor $FeSe_{0.4}Te_{0.6}$</i>	30
L. Isac, A. Duta <i>Copper sulfides as materials with promising potential in dyes photodegradation</i>	30
B. D. Klee, J. R. Stellhorn, S. Hosokawa, M. Krbal, N. Boudet, N. Blanc, W.-C. Pilgrim <i>Structure determination of amorphous $(Ga_2Se_3)_{25}(GeSe_2)_{75}$ by anomalous X-ray scattering</i>	31
P. Kostka, M. Iezid, O.Bošák, R. Yatskiv, J. Zavadil, N. Bašinová, M. Legouera, M. Kubliha, D. Le Coq <i>Optical and electrical properties of Sb_2O_3-$ZnBr_2$ oxybromide glasses</i>	32
O. Kondrat, R. Holomb, A. Csik, V. Takáts, M. Veres, N. Tsud, M Vondráček, V. M. Mitsa <i>In situ versus ex situ investigations of the As_2S_3 nanolayers modified by near bandgap laser treatment</i>	32
Amera Z. Mahmoud <i>Effect of composition and thermal annealing on the electrical conduction of $Se_{85-x}Te_{15}Sb_x$ glasses</i>	33
V.S. Minaev, S.P. Timoshenkov, S.N. Novikov, N.E. Korobova, V.V. Kalugin <i>Genesis of nanoheteromorphous glassforming melt and process of glass transition</i>	34
V. Mitsa, A. Feher, S. Petretskij, R. Holomb, V. Tkac <i>Hysteresis of low temperature thermal conductivity, Boson peak in glassy (g) As_2S_3 and low frequency ring and branched As_mS_m clusters vibrations</i>	34
S. Molnar, V. Takacs, R. Bohdan, S. Misak, I. Csarnovics, Y. Kaganovsky, S. Kökényesi <i>Investigations of phase-modulated optical recording in amorphous chalcogenide layers from As-Se-Te system</i>	35
M. Reinfelde, Z. Ivanova, M. Mitkova, T. Nichol, J. Teteris <i>Photoinduced mass transport in Ge-Se amorphous films</i>	36
S. A. Sergheev, O. V. Iaseniuc, M. S. Iovu <i>Electron-beam recording of diffractive gratings in $(As_4S_3Se_3)_{1-x}Sn_x$ amorphous thin films</i>	36
O. Shylenko, V. Bilanych, A. Feher, V. Rizak, V. Komanicky <i>Comparison of sensitivity of $Ge_9As_9Se_{82}$ and $Ge_{16}As_{24}Se_{60}$ thin films to irradiation with electron beam</i>	37
F. Skuban, S. R. Lukić-Petrović, M. V. Šiljegović, D. M. Petrović, M. Slankamenac <i>Study of dielectric properties of some bulk Cu-As-Se-I chalcogenides</i>	38
I. Studenyak, V. Izai, A. Bendak, P. Kúš, S. Kökényesi <i>High-conductive Cu_6PS_5I-based thin films: structural, electrical and optical properties</i>	38
V. J. Sukyte, L. Samardokas, R. Ivanauskas, A. Ivanauskas, I. Ancutiene <i>Review of physical-chemical properties and applications of chalcopolythionic acids</i>	39
N. Tanwar, V. K. Saraswat <i>Study the entropy change in glassy region under non-isothermal conditions for $Ge_{25-x}Se_{75}Sb_x$ ($x = 12, 15$ and 18) chalcogenide glasses</i>	40

A. Velea, G. Socol, C. Mihai, A. Lőrinczi, I. D. Simandan, G. Schinteie, F. Sava
Thermal stability of heterojunction interfaces in GaSb/GeTe, GaSb/SnSe and SnSe/GeTe bilayers.....40

I. M. Wanjiku
Crystallization kinetics of In-Se chalcogenide glasses for phase change memory (PRAM) applications41

Author Index43

manner in chessboard-like arrangement. Our result is explained by the formation of charge distribution bilayer under electron irradiation of chalcogenide films and subsequent flow of the self-consistent currents generated in irradiated area. The size of the interaction region of the EB with $\text{Ge}_9\text{As}_9\text{Se}_{82}$ film has been determined ($6.2\mu\text{m}$). The appearance of surface relief is associated with formation into film the space charge region (SCR) induced by EB. We find that when matrix period is of comparable with size SCR the chessboard-like lattice is formed in films with thickness larger than $3\mu\text{m}$ by the overlap of neighboring space charge regions in irradiated areas. When matrix period is larger than SCR surface reliefs generated in single step charge deposition step are identical. When film thicknesses is $4.5\mu\text{m}$ and matrix period is $10\mu\text{m}$ parameters of electron-induced relief reach gigantic values: cone height - 3880nm , depth of crater - 1310nm . We demonstrate that by variation of lattice period during periodic charge deposition in chalcogenide thin films we could directly experimentally define SCR size in these materials.

Relaxation processes in chalcogenide glasses

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Relaxation processes in chalcogenide glasses of the Se, As-Se, Ge-As-Se systems have been investigated by dynamic mechanical analysis technique. Temperature dependence of internal friction and real and imaginary parts of the shear modulus of chalcogenide glasses were measured in the mode of forced torsional and bending vibrations. In selenium-rich glasses of As-Se and Ge-As-Se systems was found maxima of internal friction and of shear modulus imaginary part in the temperature range 200K-250K. This relaxation process can be identified as β -process of mechanical relaxation. Its activation energy lie in the range of 0.5-1 eV. Parameter relaxation time distribution was determined from the cole-cole diagram (0.15-0.2). We shown that the cause of β -process of these glasses can be relaxation of their structure in region of local disordering in the vicinity of selenium atoms with dangling bonds, as well as the fluctuation microcavities. The relaxation maximum of internal friction is observed in the glass transition temperature for all glasses under investigation. This relaxation process was classified as α -process of mechanical relaxation these glasses. This process is caused by complete defreezing of the mobility of glass structural elements. Highelasticity plateau is observed on the temperature dependence of the shear modulus in Se-rich glasses of Ge-As-Se system as well as in Se and in glasses As-Se systems. Parameter relaxation time distribution was determined from the Cole-Cole diagrams. It was found that the full relaxation spectrum of chalcogenide glasses formed three relaxation processes: α -relaxation is determined by full unfreezing of mobility of the structure units and the transition of glasses into the heighelastic state; β -relaxation which can be associated with the relaxation of glass structure in regions of local disordering in the vicinity of atoms with unsaturated (dangling) bonds; γ -relaxation of selenium is determined by the twolevel systems in the atomic twohole potential.

Ultrasound modulation of the structure of glassy chalcogenides

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Our previous experiments on ultrasonic treatment of the softening Se-X glasses (X= Te, S, As, Cl) [1-4] are reconsidered here using a special representation of the optical transmission data for the Se-Te series as an example. The obtained results lead to the conclusion that glass behaves as the *self-organizing* system of the dissipative type. A characteristic dissipative pattern is considered as the *bond wave* [5], whose wavefronts